









GENERAL PURPOSE OF THE CONFERENCE

The aim of **ESSCIRC** and **ESSDERC** is to provide an annual European forum for the presentation and discussion of recent advances in solid-state devices and circuits. The level of integration for system-on-chip design is rapidly increasing. This is made available by advances in semiconductor technology. Therefore, more than ever before, a deeper interaction among technologists, device experts, IC designers and system designers is necessary.

ESSCIRC and **ESSDERC** are governed by a common Steering Committee and share Plenary Keynote Presentations and Joint Sessions bridging both device and circuit communities. Attendees registered for either conference are encouraged to attend any of the scheduled parallel sessions, regardless to which conference they belong.

CONFERENCE HIGHLIGHTS

- 3 joint keynote presentations
- 4 **ESSCIRC** keynote presentations
- 3 ESSDERC keynote presentations
- Invited papers with overall coverage of all aspects of advanced devices and circuits
- Presentation of IEEE and ESSCIRC/ESSDERC Awards ESSCIRC/ESSDERC Gala Dinner on Wednesday, September 13, 2023
- Tutorials and workshops

ESSCIRC/ESSDERC evolves, following recent R&D device/ circuit fast-growing topics, and creating even more interactions between circuit and device as well as memory and logic researchers. Technical Program Committee tracks have been re-organized accordingly and joint tracks between **ESSCIRC** and **ESSDERC** will be proposed.

The working language of the conference is English.



















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CONFERENCE TRACKS

Although not limited, papers are solicited for the following main topics:

- Advanced Technology, Process and Materials Process and material developments for logic, memory, and non-CMOS, including electrical and physico-chemical characterization, process integration and manufacturing: 2D TMDs and related insulators (e.g., hBN), graphene, TFTs, gate oxide, gate material, silicide, MOL and BEOL materials, 3D monolithic as well as conventional and novel memory cells including charge-based memories, ReRAM, MRAM, PCRAM, ferroelectrics, crosspoint and selectors, organic memory.
- Analog, Power and RF Devices From material growth to device, components, and systems (process, design, devices fabrication, applications). Device design and electrical/physical/electro-thermal/reliability characterization of devices based on Si RF CMOS, RF SOI, SiGe HBTs, SiC, InP/InGaAs/GaAs, AlGaN/InGaN/GaN, CNT, diamond and related material systems. Power systems integration issues including thermal management, packaging technologies, system-level electro thermal characterization, product quality and system reliability aspects. Device production processes and design for manufacturability.
- Compact modeling and process/device simulation TCAD and advanced simulation techniques and studies, compact/ SPICE modeling of electronic, optical, organic, emerging, and hybrid devices and their IC implementation and interconnection. Verilog-A models of semiconductor devices (including bio/med sensors, MEMS, microwave, RF, high voltage and power, emerging technologies, and novel devices), parameter extraction, reliability and variability, performance evaluation and open-source benchmarking/implementation methodologies. Modeling of interactions between process, device and circuit design, design/technology co-optimization, foundry/fabless interface strategies. Numerical, analytical, statistical modeling and simulation of electronic, optical and hybrid devices, interconnect, isolation, and 2D/3D integration. Simulations of material properties and fabrication processes. Advanced physical phenomena (quantum mechanical and non-stationary transport phenomena, ballistic transport). Mechanical and/or electro-thermal modeling and simulation. Simulations of reliability aspects of materials and devices.
- Analog Amplifiers, drivers, comparators, filters, references, analog systems, and analog techniques.
- Data Converters Nyquist-rate and oversampling A/D and D/A converters. Capacitance-to-digital, time-to-digital, frequency-todigital converters. Embedded and application-specific A/D and D/A converters. Analog to information conversion. A/D and D/A converter building blocks (sample-and-hold circuits, calibration circuits). Enabling new techniques, architectures, or technologies.
- RF & mm-Wave Building blocks operating at RF, mm-Wave and THz frequencies for wireless communication, radar, sensing, and imaging.
- Frequency Generation Circuits Oscillators and controlled oscillators, PLL, DLL, injection locked oscillators, frequency dividers, any kind of frequency generation or time base circuits and systems.
- Digital Circuits & Systems Digital circuits and memory subsystems for microprocessors, micro-controllers, application processors, graphics processors; digital systems for communications, video, and multimedia. Digital design techniques for power reduction, intra-chip communication, clock distribution, soft-error and variation-tolerant design, system-level integration.
- Power Management Power management and control circuits. Regulators. Switched-mode power converter ICs using inductive, capacitive, and hybrid techniques. Energy harvesting circuits and systems. Wide-bandgap topologies and gate-drivers. Power and signal isolators; robust power management circuits for automotive and other harsh environments. Circuits for lighting, wireless power and envelope modulators. Design for manufacturability
- Wireless & Wireline Circuits & Systems Wireless and wireline circuits and systems, 2.5/3D interconnect, copper-cable links, and equalizing on-chip links, exploratory I/O circuits for advancing data rates, radio transceiver SoC or SiP at RF/mmW and THz frequencies, chip to chip system communications, high speed serial interfaces, optical interfaces, established standards communication system full chip solutions.
- Emerging and in-memory Computing Devices and Circuits Advanced CMOS, post-CMOS, quantum computing, cryogenic circuits, novel device and circuit concepts that improve existing and enable novel computing paradigms. Advanced CMOS and beyond CMOS transistors (tunnel FET, negative capacitance FET), transistors based on low-dimensional systems (2D materials, nanowires, and quantum dots), and on topological insulators, as well as phase transitions transistors and all kind of circuit implementations with such devices. Qubit devices for quantum computing enabling and all related cryogenic circuits. Non-charge-based logic devices and circuits (magnetic logic, spintronics, and plasmonics).
- Devices & Circuits for AI and ML Neuromorphic computing, AI accelerators, in-memory-computing, security. Emerging devices and
 materials in neuromorphic computing. New materials, and new uses for established materials, within the context of neuromorphic
 computing algorithms, ranging from deep neural networks (deep learning) to more bio-inspired networks and algorithms. Resistive
 switching materials, including phase change and ferroelectric materials for neuromorphic computing, materials for spintronic
 implementations of neuromorphic computing. Edge and cloud AI computing platforms. Silicon implementation of neuromorphic
 circuits, processors, systems and their applications. In-memory-computing and logic-in-memory. Phenomena, devices, circuits, and
 systems for IoT and IoE security (e.g., PUFs, TRNGs).
- Devices & Circuits for Sensors, Optoelectronics & Display Devices and circuits based on MEMS and bioelectronics devices for biomedical and imaging applications. Image sensors and related circuits and systems, SoCs. Automotive, LIDAR, and ultrasonic sensors for ADAS, autonomous driving, smart mobility. MEMS sensor systems. Wearable, implantable, ingestible electronics, biomedical SoCs, neural interfaces and closed-loop systems. Biosensors, microarrays, and lab-on-a-chip. Display electronics, displays with sensing functionality. Devices, circuits, and systems for AR/VR and related sensing/actuation. Product quality and reliability aspects. Device and circuits production processes and design for manufacturability

PAPER SUBMISSION

Manuscript guidelines as well as instructions on how to submit electronically will be available on the conference website. Papers must not exceed four A4 pages with all illustrations and references included.

PAPERS SUBMISSION DEADLINE: APRIL 14, 2023

Papers submitted for review must clearly state:

- The purpose of the work
- How and to what extent it advances the state-of-the art
- Specific results and their impact

Only work that has not been previously published or submitted elsewhere will be considered. Submission of a paper for review and subsequent acceptance is considered as a commitment that the work will not be publicly available prior to the conference.

After selection of papers, the authors will be informed about the decision of the Technical Program Committee by e-mail by 24 May 2023.

At the same time, the complete program will be published on the conference website.

An oral presentation will be given at the Conference for each accepted paper. No-shows will result in the exclusion of the papers from any conference related publication.

The submitted final PDF files should be IEEE Xplore compliant.

For each paper independently, at least one (co-)author is required to register for the Conference (**one registration-one paper policy**). Registration fees and deadlines will be available on the conference website.

BEST PAPER AWARD

Papers presented at the conference will be considered for the "Best Paper Award" and "Best Young Scientist Paper Award". The selection will be based on the results of the paper selection process and the judgment of the conference participants. The award delivery will take place during **ESSCIRC**/ESSDERC 2024.

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